

**Small Signal Transistors**  
**NPN - Silicon RF Transistor Chip**

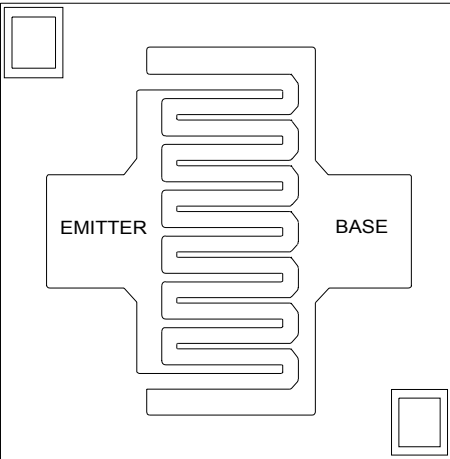
**PROCESS DETAILS**

PROCESS	EPITAXIAL PLANAR
DIE SIZE	15 x 15 MILS
DIE THICKNESS	7.5 MILS
BASE BONDING PAD AREA	2.0 x 2.4 MILS
EMITTER BONDING PAD AREA	2.0 x 2.7 MILS
TOP SIDE METALIZATION	Al
BACK SIDE METALIZATION	Au - 16,000Å

**PRINCIPAL DEVICE TYPES**

2N3866

**GEOMETRY**



BACKSIDE COLLECTOR

Please refer to  
selection guide on page 19.

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